

SEMI E113-0306 (Reapproved 0518) SPECIFICATION FOR SEMICONDUCTOR PROCESSING EQUIPMENT RF POWER DELIVERY SYSTEMS

This Standard was technically approved by the global Metrics Technical Committee. This edition was approved for publication by the global Audits and Reviews Subcommittee on December 13, 2017. Available at www.semiviews.org and www.semi.org in May 2018; originally published November 2001; previously published May 2012.

1 Purpose

1.1 Process plasmas are used throughout the semiconductor industry for the etching and deposition of thin films. The majority of the process chambers use radio frequency (RF) power to produce and sustain the plasmas. Because the reliability and repeatability of the plasma directly impacts wafer-processing results, RF power delivery systems are a key element of semiconductor manufacturing technology. The accurate and reproducible performance of the entire RF power generation system, including the RF-influenced parameters of the plasma, must be within commonly accepted tolerances.

1.2 Design criteria for RF reliability and repeatability demand standardized testing and evaluation of the performance of the RF power delivery systems and control instrumentation on a chamber. Not only must the subsystems (i.e., the generator, cable assemblies, matching network, chuck/coil) be characterized, but the performance of the integrated system must also be characterized over the intended operating range.

1.3 It is the intent of this Standard to provide RF power delivery specifications for semiconductor processing equipment that leads to improved system and subsystem performance. It outlines performance criteria as well as required documentation that must be supplied with the system or subsystem components. The goal of the Document is to provide the specifications needed to produce a well-characterized RF power delivery system, where stability, repeatability, and important electrical parameters such as delivered power, current/voltage, and the impedance of the system can be determined within the operating space.

2 Scope

2.1 This Standard specifies the minimum performance criteria for RF equipment used in the semiconductor industry. It does not address specific test methods or procedures for performance verification.

2.2 The primary focus for this Specification is semiconductor processing equipment including, but not limited to, the following tool types:

- Dry etch equipment, and
- Film deposition equipment (chemical vapor deposition [CVD] and physical vapor deposition [PVD]).

2.3 This Specification applies to semiconductor processing equipment RF power delivery systems whose power is directly used to produce and sustain the plasma.

NOTICE: SEMI Standards and Safety Guidelines do not purport to address all safety issues associated with their use. It is the responsibility of the users of the Documents to establish appropriate safety and health practices, and determine the applicability of regulatory or other limitations prior to use.

3 Limitations

3.1 This Standard is meant to address RF systems that primarily operate in the frequency range of 0.2 to 100 MHz. It does not address higher frequency RF systems or microwave systems.

3.2 This Standard is not meant to address pulsed-power RF systems.

3.3 This Standard is intended to be a performance Specification and is not intended to address design issues related to safety, which are covered elsewhere in the SEMI Standards.

3.4 This Standard does not address any safety or performance issues related to RF emissions or electrical codes (e.g., Underwriter's Laboratory, Inc. [UL], the National Electrical Code [NEC], Federal Communications Commission

[FCC]). It is the responsibility of the users of this Standard to conform to the appropriate local codes and regulations as applied to this type of equipment, some of which are covered by referenced Documents.

4 Referenced Standards and Documents

4.1 SEMI Standards and Safety Guidelines

SEMI E10 — Specification for Definition and Measurement of Equipment Reliability, Availability, and Maintainability (RAM) and Utilization

SEMI E78 — Guide to Assess and Control Electrostatic Discharge (ESD) and Electrostatic Attraction (ESA) for Equipment

SEMI E114 — Test Method for RF Cable Assemblies Used in Semiconductor Processing Equipment RF Power Delivery Systems

SEMI E115 — Test Method for Determining the Load Impedance and Efficiency of Matching Networks Used in Semiconductor Processing Equipment RF Power Delivery Systems

SEMI E135 — Test Method for RF Generators to Determine Transient Response for RF Power Delivery Systems used in Semiconductor Processing Equipment

SEMI E136 — Test Method for Determining the Output Power of RF Generators Used in Semiconductor Processing Equipment RF Power Delivery Systems

4.2 IEEE Standards¹

IEEE-STD-383 — IEEE Standard for Type Test of Class 1E Electrical Cables, Field Splices, and Connections for Nuclear Power Generating Stations

4.3 United States Military Standards²

MIL-DTL-17 — General Specification for Cables, Radio Frequency, Flexible and Semi Rigid

MIL-PRF-39012D — General Specification for Connectors, Coaxial, Radio Frequency

NOTICE: Unless otherwise indicated, all documents cited shall be the latest published versions.

5 Terminology

5.1 Abbreviations and Acronyms

5.1.1 *CVD* — chemical vapor deposition

5.1.2 *DC* — direct current

5.1.3 *IEEE* — Institute of Electrical and Electronics Engineers

5.1.4 *MIL* — United States Military Standards

5.1.5 *PVD* — physical vapor deposition

5.1.6 *RF* — radio frequency

5.1.7 *VSWR* — voltage standing wave ratio

5.2 Definitions

5.2.1 *cable assembly* — the section of cable (transmission line), including the connectors, used to connect various parts of the RF power delivery system.

5.2.2 *electrical length* — the length of the cable assembly at the operating frequency expressed in terms of degrees, where one wavelength at the nominal operating frequency is equal to 360°.

¹ Institute of Electrical and Electronics Engineers, 3 Park Avenue, 17th Floor, New York, NY 10016-5997, USA; Telephone: +1.212.419.7900, Fax: +1.212.752.4929, <http://www.ieee.org>

² United States Military Standards, available through <http://everyspec.com>

5.2.3 *harmonic frequency* — the harmonic frequencies are defined as integer multiples of the fundamental frequency. For example, the second harmonic of 13.56 MHz is 27.12 MHz.

5.2.4 *load Q* — the quality factor, Q , of the load is defined here as the magnitude of the reactive part of the load divided by the real part of the load. For example, a load impedance of $2 + j20 \Omega$ would have a load Q of 10.

5.2.5 *matched load* — a matched load impedance is defined as typically having a magnitude of $50 \pm 3.3 \Omega$ at a phase angle of up to $\pm 3.8^\circ$. In other words, the load is considered matched if the reflection coefficient is no greater than 0.032 at any phase angle.

5.2.6 *matching network* — the device used to transform the impedance of the load (chamber/chuck) to match the impedance of the generator/cable assembly, which is typically 50Ω .

5.2.7 *matching network load impedance* — the impedance of the load to which the matching network is matched.

5.2.8 *MTBF_p* — mean productive time between failures; the average time the equipment performed its intended function between failures per SEMI E10; productive time divided by the number of failures during that time. Only productive time is included in this calculation.

5.2.9 *power efficiency* — the power efficiency of a matching network is defined as the power exiting the network (output power) divided by the power entering the network (input power).

5.2.10 *RF applicator/interface* — the part of the chamber where the RF system is terminated. This interface can either be a chuck (driven electrode) or the coil/antenna part of a plasma source.

5.2.11 *RF system* — the RF system is defined as the combination of the generator, matching network, chamber interface, and the associated connecting cable assemblies that are specific to a particular tool/chamber.

5.2.12 *tap point* — for some systems, partial tuning of the matching network is achieved by switching in a combination of fixed tuning elements, such as different values of capacitors. The tap point is defined as the position of the switch(es) that connect or disconnect tuning elements in the matching network circuit.

5.2.13 *tuning element position* — the position of the tuning element is defined as the output voltage or output encoder value that corresponds to the position of a variable tuning element in a matching network. For example, the voltage from a rotary potentiometer on the rotating shaft of a variable capacitor (the 'tuning element') would be referred to as the capacitor's 'position'. In this example, the position/voltage corresponds to a certain shaft location or position.

5.3 Symbols

5.3.1 *cm* — centimeter

5.3.2 *db* — decibel

5.3.3 *j* — imaginary unit

5.3.4 *kW* — kilowatt

5.3.5 *MHz* — megahertz

5.3.6 Ω — ohm

5.3.7 *Q* — quality factor

5.3.8 *s* — second

5.3.9 *W* — watt

6 Ordering Information

6.1 Semiconductor manufacturers may use this Standard when procuring processing equipment to specify RF power delivery system performance and documentation. The equipment suppliers may also use this Document to specify the RF system components and subassemblies.

6.2 Orders for equipment in accordance with this Standard shall include:

6.2.1 This Specification number and date of issue.

6.2.2 Any certification showing passage of qualification tests required to be provided (optional).

6.2.3 Any test results required to be included in reports to be provided (optional).

7 Requirements

7.1 Semiconductor processing equipment shall be designed and built with a reliable RF power delivery system. The requirements defined in this Specification address the integrated RF system as well as the following RF power delivery system components: the RF cable assemblies, the matching network, the generator, and the RF applicator/interface, as well as specific components of these assemblies or systems.

7.2 The mean (productive) time between failures (MTBF_p), as outlined in SEMI E10, of the generator, matching network, and the RF power delivery system as a whole shall be provided by the supplier, as well as the test method used to determine MTBF_p.

7.3 RF Cable Assemblies (Transmission Lines)

7.3.1 Many RF power delivery systems use RF cable assemblies to transfer power from the generator to the input of the matching network and, in some cases, from the output of the matching network to the process chamber (e.g., the chuck assembly). All cable assemblies shall adhere to industry standards for cables and connectors (e.g., MIL-DTL-17, MIL-PRF-39012D, IEEE-STD-383) in terms of rated power/voltage/current, allowed bending radius, expected variation in characteristic impedance, and attenuation at the expected operating frequency(s) for the specific cable type (e.g., RG-217, RG-218) per the cable manufacturer's specifications. SEMI E114 or an equivalent test method(s) shall be used to determine the electrical length, power dissipation (loss), and characteristic impedance of the RF cable assemblies.

7.3.2 The length of the cable assemblies used to connect portions of the RF power delivery system shall be specified in terms of electrical length at the nominal operating frequency, in addition to the nominal physical length. The electrical length shall be given in terms of degrees of phase shift. Variations in the dielectric properties (e.g., phase velocity, characteristic impedance) of the cable assemblies can cause the electrical length to differ between assemblies.

7.3.3 The electrical length of cables used between the matching network and the chamber (if any) shall be specified to within 0.25° of the standard electrical length value at the operating frequency for fixed frequency systems or at the midpoint frequency for variable frequency systems, for frequencies less than or equal to 13.56 MHz. For frequencies above 13.56 MHz, the length should be specified to a value (in degrees) equal to the frequency in MHz multiplied by 0.018 (e.g., the specification for 60 MHz would be $60 \times 0.018 = 1.1^\circ$). For example, at 13.56 MHz, the physical length of typical cable (RG-217) corresponding to 0.25° of phase shift (0.5° of reflection coefficient phase shift) would be approximately 1 cm. This specification would result in impedance variations seen by the matching network of less than approximately 1% between processing chambers.

7.3.4 The length of cables used between the matching network and the generator shall be specified to within 1.0° of the standard electrical length value at the operating frequency for fixed frequency systems or at the midpoint frequency for variable frequency systems, for frequencies less than or equal to 13.56 MHz. For frequencies above 13.56 MHz, the length shall be specified to a value (in degrees) equal to the frequency in MHz multiplied by 0.074 (e.g., the specification for 60 MHz would be $60 \times 0.074 = 4.44^\circ$). For example, at 13.56 MHz, the physical length of typical cable (RG-217) corresponding to 1.0° of phase shift (2.0° of reflection coefficient phase shift) would be approximately 4 cm. This specification would minimize the impedance transformation at the harmonic frequencies (10° of phase shift at the 10th harmonic frequency).

7.3.5 The expected power dissipation in the cable assembly(s) supplied with the system shall be provided as a function of the operating frequency(s) of the system. The amount of power transmitted through the cable assembly shall be given in terms of dB (decibels) and percentage. The relationship between dB and percentage is given as:

$$\text{Percentage} = 100 \times 10^{(\text{dB}/10)}$$

For example, approximately 94.8% (−0.232 dB of loss) of the power at 13.56 MHz will be transmitted through a cable assembly made from RG-217 cable with a physical length of 15.24 meters (electrical length of 375.74°). In other words, 5.2% of the power is dissipated in the cable assembly at 13.56 MHz.

7.4 Matching Networks

7.4.1 Matching networks transform the impedance of the plasma load to match the impedance of the generator, which is nominally 50 Ω. The transformation is achieved by the use of various reactive components, such as capacitors and inductors, that 'tune' the matching network by transforming the impedance at the output of the network to the input